

ABSTRACT OF THE DISCLOSURE

A Group-III nitride semiconductor device including a crystal substrate, an electrically conducting Group-III nitride semiconductor ($\text{Al}_x\text{Ga}_y\text{In}_{1-(x+y)}\text{N}$: $0 \leq x < 1$, $0 < y \leq 1$ and $0 < x+y \leq 1$) crystal layer vapor-phase grown on the crystal substrate, an ohmic electrode and an electrically conducting boron phosphide crystal layer provided between the ohmic electrode and the Group-III nitride semiconductor crystal layer, the ohmic electrode being disposed in contact with the boron phosphide crystal layer. Also disclosed is a method for producing the Group-III nitride semiconductor device, and a light-emitting diode including the Group-III nitride semiconductor device.